

BAV19 / 20 / 21



DO-35 Color Band Denotes Cathode

Small Signal Diode

Absolute Maximum Ratings*

 $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{RRM}	l	BAV19 BAV20 BAV21	120 200 250	V V V
I _{F(AV)}	Average Rectified Forward Current		200	mA
I _{FSM}	Non-repetitive Peak Forward Surge Current Pulse Width = 1.0 second Pulse Width = 1.0 microsecond		1.0 4.0	A A
T _{stg}	Storage Temperature Range	-65 to +200	°C	
T _J	Operating Junction Temperature	175	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics

Symbol	Parameter	Value	Units
P_{D}	Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	300	°C/W

Electrical Characteristics T₄ = 25°C unless otherwise noted

Symbol	Parameter		Test Conditions	Min	Max	Units
V_R	Breakdown Voltage	BAV19	I _R = 100 μA	120		V
		BAV20	$I_R = 100 \mu A$	200		V
		BAV21	I _R = 100 μA	250		V
V_{F}	Forward Voltage		$I_F = 100 \text{ mA}$		1.0	V
			$I_F = 200 \text{ mA}$		1.25	V
I _R	Reverse Current		V _R = 100 V		100	nA
		BAV19	$V_{B} = 100 \text{ V}, T_{A} = 150^{\circ}\text{C}$		100	μΑ
			$V_{B} = 150 \text{ V}$		100	nА
		BAV20	$V_{\rm B} = 150 \text{ V}, T_{\rm A} = 150^{\circ}\text{C}$		100	μΑ
			V _B = 200 V		100	nA
		BAV21	$V_{R} = 200 \text{ V}, T_{A} = 150^{\circ}\text{C}$		100	μΑ
C _T	Total Capacitance		$V_R = 0, f = 1.0 \text{ MHz}$		5.0	pF
t _{rr}	Reverse Recovery Time		$I_F = I_R = 30 \text{ mA}, I_{RR} = 3.0 \text{ mA},$		50	ns
	_		$R_L = 100\Omega$			

¹⁾ These ratings are based on a maximum junction temperature of 200 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Small Signal Diode

(continued)

Typical Characteristics

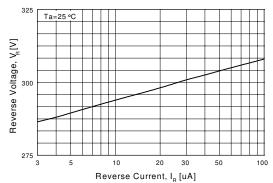
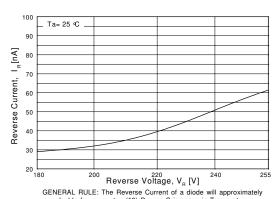


Figure 1. Reverse Voltage vs Reverse Current BV - 1.0 to 100uA



GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

Figure 3. Reverse Current vs Reverse Roltage

IR - 180 to 225 V

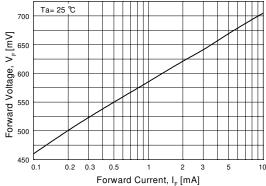
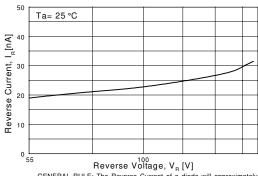


Figure 5. Forward Voltage vs Forward Current VF - 0.1 to 10mA



GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

Figure 2. Reverse Current vs Reverse Voltage IR - 55 to 205 V

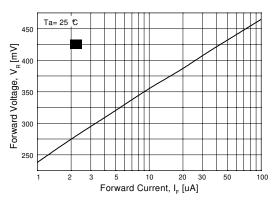


Figure 4. Forward Voltage vs Forward Current VF - 1.0 to 100uA

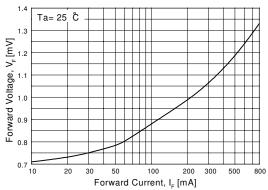


Figure 6. Forward Voltage vs Forward Current VF - 10 to 800mA

Small Signal Diode

(continued)

Typical Characteristics (continued)

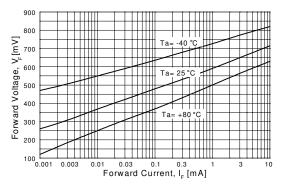
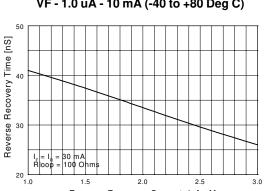


Figure 7. Forward Voltage vs Ambient Temperature VF - 1.0 uA - 10 mA (-40 to +80 Deg C)



Reverse Recovery Current, I_m [mA]

Figure 9. Reverse Recovery Time vs
Reverse Recovery Current

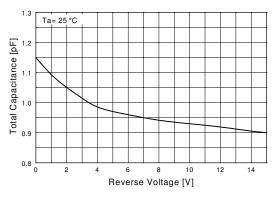


Figure 8. Total Capacitance

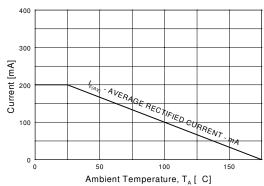


Figure 10. Average Rectified Current ($I_{F(AV)}$) versus Ambient Temperature (T_{Δ})

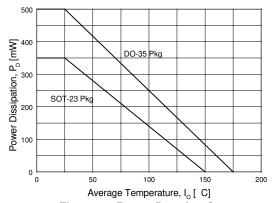


Figure 11. Power Derating Curve

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